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FABRICATION METHOD OF NITRIDE SEMICONDUCTORS AND NITRIDE  
SEMICONDUCTOR STRUCTURE FABRICATED THEREBY

Docket No. 2336-254

Inventor: Sun Woon KIM et al.

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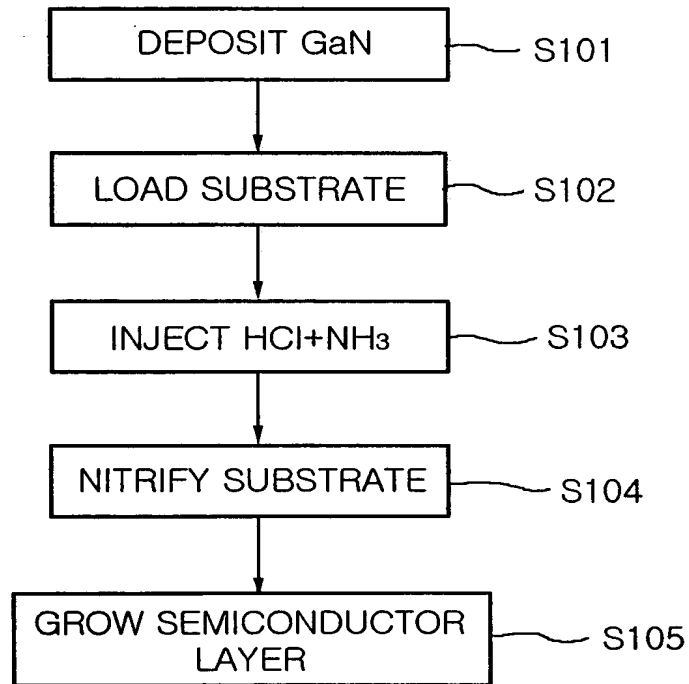


FIG. 1

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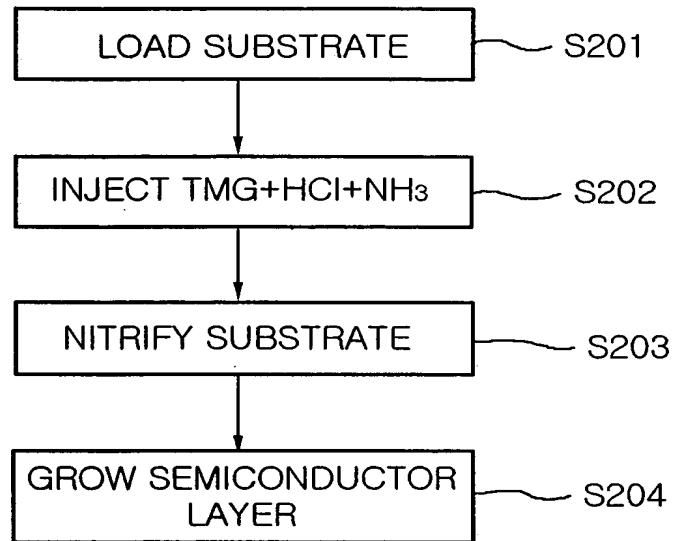


FIG. 2

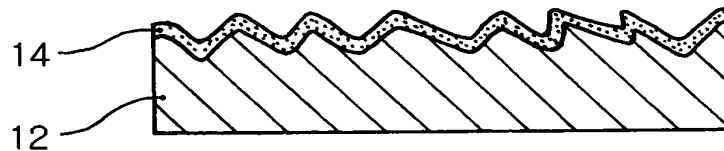


FIG. 3

FABRICATION METHOD OF NITRIDE SEMICONDUCTORS AND NITRIDE  
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X 1.000nm /div  
Z 20.000nm /div

FIG. 4

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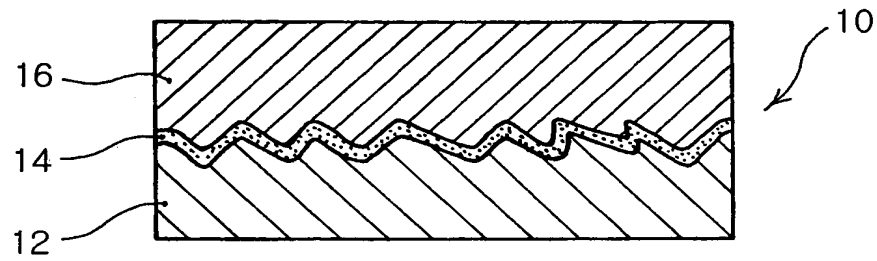
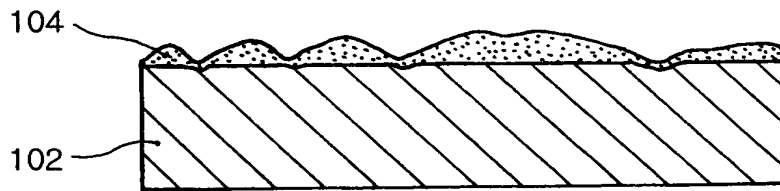


FIG. 5



PRIOR ART

FIG. 6

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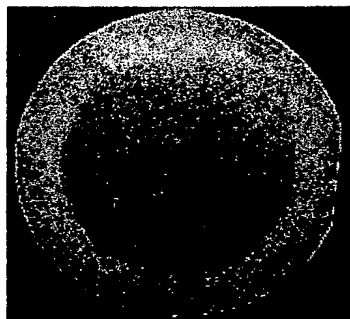
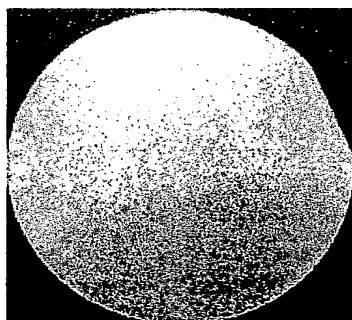
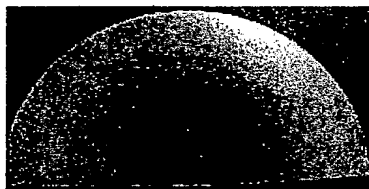


FIG. 7



PRIOR ART

FIG. 8



PRIOR ART

FIG. 9